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TC 1700PATENT
5298-03500/PM99021

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8/w.m.
7/24/01**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**In re Application of:
Lau

Serial No.: 09/476,669

Filed: December 30, 1999

For: METHOD FOR FORMING A
METALLIZATION STRUCTURE
IN AN INTEGRATED CIRCUIT

Group Art Unit: 1753

Examiner: Cantelmo, G.

Atty. Dkt. No: 5298-03500

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TC 1700**CERTIFICATE OF MAILING**
37 C.F.R. § 1.8I hereby certify that this correspondence is being deposited with
the U.S. Postal Service with sufficient postage as First Class
Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on the date indicated below:

7/12/01

Kevin L. Daffer

DECLARATION UNDER 37 C.F.R. 1.131Commissioner for Patents
Washington, D.C. 20231

I, Gorley L. Lau, hereby declare and state that:

1. I am a named inventor in the above-identified patent application, which is a U.S. patent application, Serial No. 09/476,669, filed December 30, 1999.
2. I have been informed that in the present application, certain claims have been rejected on reference to Sundarrajan, U.S. Patent No. 6,177,350, issued January 23, 2001, filed April 14, 1998.



CONCEPTION AND REDUCTION TO PRACTICE

3. As set forth in more detail below, I conceived and reduced to practice the subject matter claimed in the present application within the United States before April 14, 1998. The subject matter includes the process of depositing a titanium wetting layer through ion metal plasma deposition and subsequently sputter depositing an aluminum layer upon the wetting layer.

4. Exhibit A attached hereto is a true copy of a presentation related to the invention which bears a date before April 14, 1998. The presentation was a status update given to employees of Cypress Semiconductor Corporation. The actual presentation date has been redacted.

5. Page 2 of Exhibit A reports that a functional titanium ion metal plasma deposition and "hot" aluminum deposition sequence had been developed prior to the date of the presentation and therefore, prior to April 14, 1998.

6. Page 5 of Exhibit A reports selected process conditions of an embodiment of such a deposition sequence using titanium ion metal plasma deposition and a two-step "cold-hot" aluminum deposition sequence (known at least within Cypress Semiconductor Corporation as "hot aluminum," "Hot Al," or the like). Such specifications include the thickness of the titanium ion metal plasma deposition layer, thickness of the cold aluminum layer, and the time and power required to deposit the hot aluminum layer.

7. The statements on Page 5 of Exhibit A indicating (i) "No" in the "Correct Config[uration]" row under the "Option 4" and "IMP Ti / Hot Al" column headings and (ii) that the titanium ion metal plasma deposition and hot aluminum deposition sequence was "(n)ot ready for manufacturing" merely denotes that the equipment at the referenced manufacturing facility did not have the proper configuration at the time of the presentation. However, another manufacturing facility within Cypress Semiconductor Corporation did have the correct configuration, and in fact, did practice the claimed invention as set forth above and in Exhibit A. Therefore, the correct configuration of the equipment was known and available prior to April 14, 1998, but just not in a high-volume production facility.

8. I hereby declare that all statements made herein of my own knowledge are true and that all statements made herein on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Date: _____

7/10/01


Gorely L. Lau